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60 V, single N-channel Trench MOSFET

29 January 2016

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	60	V	
V_{GS}	gate-source voltage			-20	-	20	V	
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	265	mA	
Static charac	Static characteristics							
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 200 mA; T_j = 25 °C		-	2.1	3.5	Ω	

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².



60 V, single N-channel Trench MOSFET

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D I
2	S	source		
3	D	drain	1 2 TO-236AB (SOT23)	G S 017aaa255

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
NX138BK	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

7. Marking

Table 4. Marking codes

Type number	Marking code [1]
NX138BK	BX%

[1] % = placeholder for manufacturing site code

60 V, single N-channel Trench MOSFET

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	60	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	265	mA
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	170	mA
		V _{GS} = 10 V; T _{sp} = 25 °C		-	330	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10$ μs		-	0.9	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	310	mW
			[1]	-	400	mW
		T _{sp} = 25 °C		-	1.67	W
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain o	liode				'	
Is	source current	T _{amb} = 25 °C	[1]	-	200	mA

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

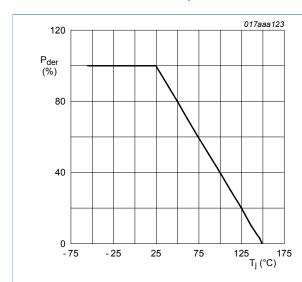


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

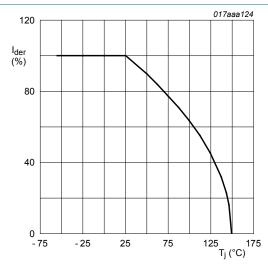


Fig. 2. Normalized continuous drain current as a function of junction temperature

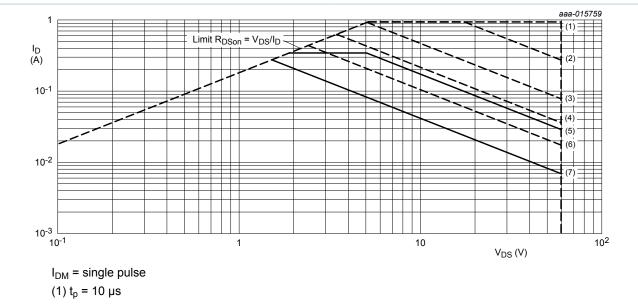
$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

NX138BK

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60 V, single N-channel Trench MOSFET



(2) $t_p = 100 \ \mu s$

(3) $t_p = 1 \text{ ms}$

(4) $t_p = 10 \text{ ms}$

(5) DC; $T_{sp} = 25 \,^{\circ}C$

(6) $t_p = 100 \text{ ms}$

(7) DC; T_{amb} = 25 °C; drain mounting pad 1 cm²

Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

60 V, single N-channel Trench MOSFET

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	350	400	K/W
			[2]	-	270	310	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	65	75	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².

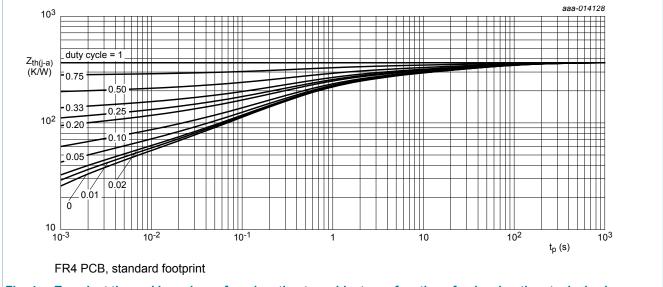
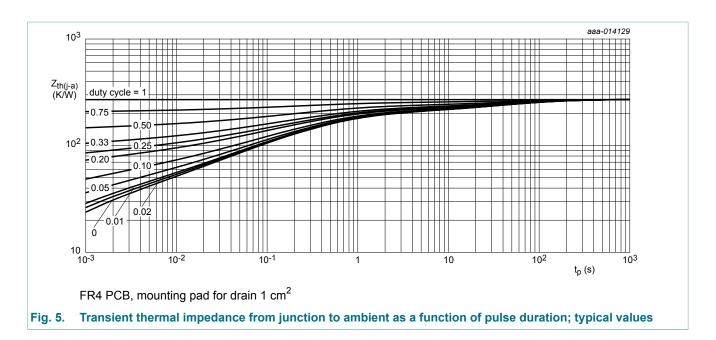


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

60 V, single N-channel Trench MOSFET



60 V, single N-channel Trench MOSFET

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.5	1	1.5	V
I _{DSS}	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μA
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-1	μA
		V _{GS} = 5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	0.3	μΑ
		V _{GS} = -5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-0.3	μA
R _{DSon}	drain-source on-state	V_{GS} = 10 V; I_{D} = 200 mA; T_{j} = 25 °C	-	2.1	3.5	Ω
	resistance	V _{GS} = 10 V; I _D = 200 mA; T _j = 150 °C	-	4.3	7.2	Ω
		V _{GS} = 5 V; I _D = 200 mA; T _j = 25 °C	-	2.2	3.8	Ω
		$V_{GS} = 2.5 \text{ V}; I_D = 75 \text{ mA}; T_j = 25 \text{ °C}$	-	2.6	5	Ω
g _{fs}	forward transconductance	V_{DS} = 10 V; I_{D} = 200 mA; T_{j} = 25 °C	-	0.71	-	S
Dynamic cl	haracteristics					
Q _{G(tot)}	total gate charge	$V_{DS} = 30 \text{ V}; I_D = 200 \text{ mA}; V_{GS} = 4.5 \text{ V};$	-	0.49	-	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.12	-	nC
Q_{GD}	gate-drain charge		-	0.12	-	nC
C _{iss}	input capacitance	$V_{DS} = 30 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	20.2	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	3.1	-	pF
C _{rss}	reverse transfer capacitance		-	2	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; I_D = 200 \text{ mA}; V_{GS} = 4.5 \text{ V};$	-	7.9	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	8.4	-	ns
$t_{\text{d(off)}}$	turn-off delay time		-	12.5	-	ns
t _f	fall time		-	5.1	-	ns
Source-dra	in diode		ı	1	1	
V_{SD}	source-drain voltage	I _S = 200 mA; V _{GS} = 0 V; T _i = 25 °C	-	0.86	1.2	V

60 V, single N-channel Trench MOSFET

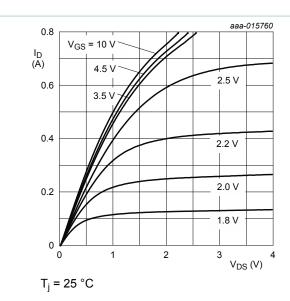


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

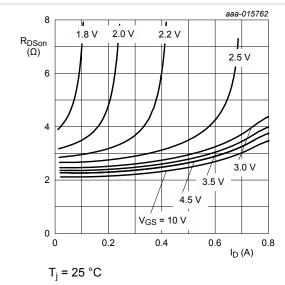


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

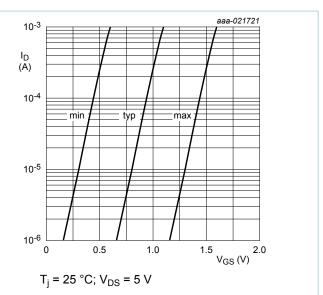
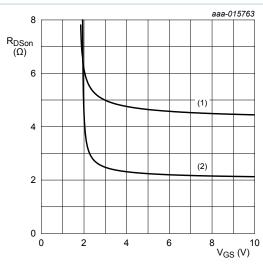


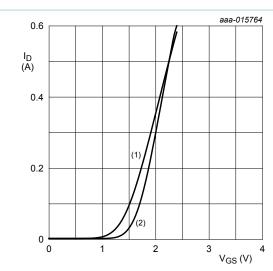
Fig. 7. Sub-threshold drain current as a function of gate-source voltage



 $I_D = 0.2 \text{ A}$ (1) $T_j = 150 \text{ °C}$ (2) $T_i = 25 \text{ °C}$

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

60 V, single N-channel Trench MOSFET



$$V_{DS} > I_D \times R_{DSon}$$

(1) $T_i = 150 \, ^{\circ}C$

(2)
$$T_i = 25$$
 °C

Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

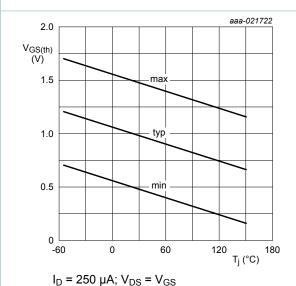


Fig. 12. Gate-source threshold voltage as a function of junction temperature

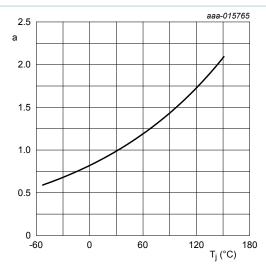
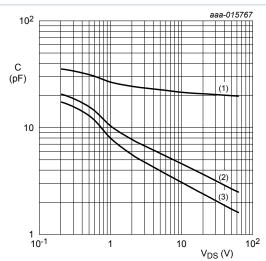


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



 $f = 1 MHz; V_{GS} = 0 V$

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

60 V, single N-channel Trench MOSFET

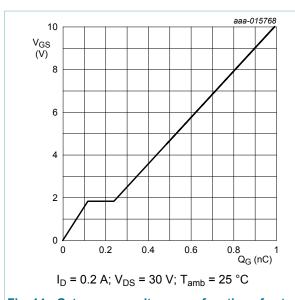


Fig. 14. Gate-source voltage as a function of gate charge; typical values

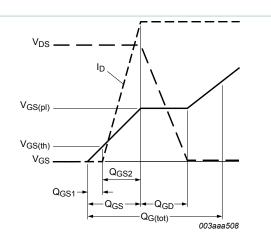
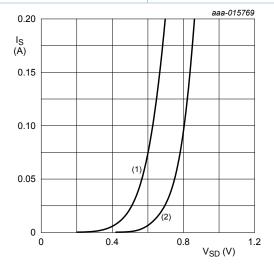


Fig. 15. MOSFET transistor: Gate charge waveform definitions



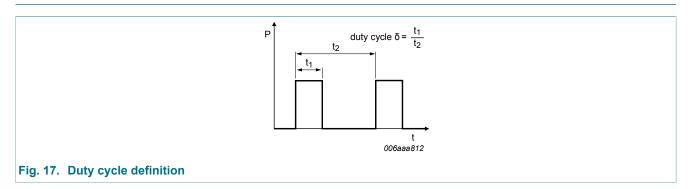
 $V_{GS} = 0 V$ (1) $T_i = 150 \,^{\circ}C$

(2) $T_i = 25 \,^{\circ}\text{C}$

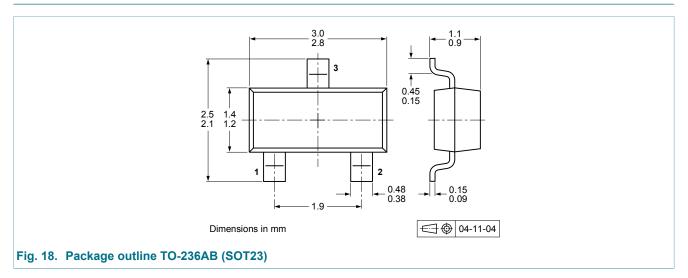
Fig. 16. Source current as a function of source-drain voltage; typical values

60 V, single N-channel Trench MOSFET

11. Test information



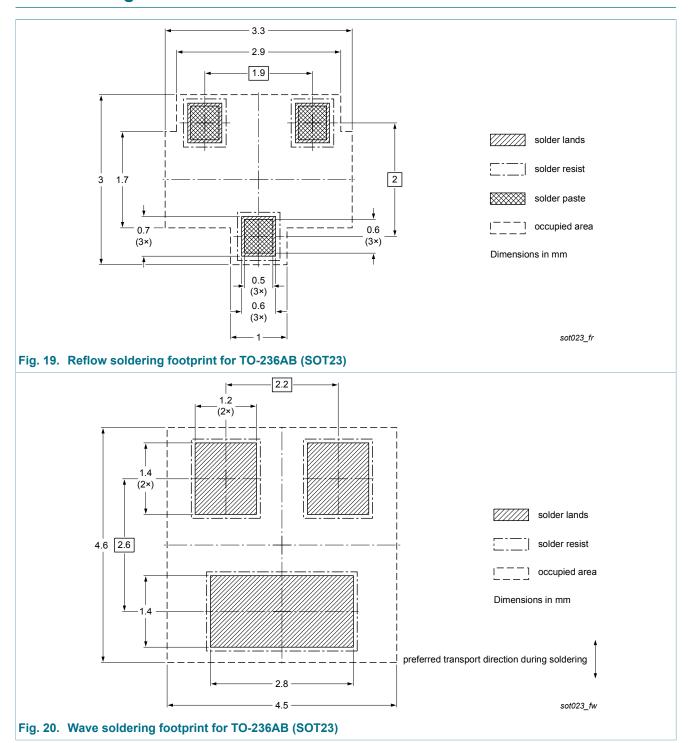
12. Package outline



11 / 16

60 V, single N-channel Trench MOSFET

13. Soldering



12 / 16

60 V, single N-channel Trench MOSFET

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
NX138BK v.1	20160129	Product data sheet	-	-

60 V, single N-channel Trench MOSFET

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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NX138BK

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60 V, single N-channel Trench MOSFET

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60 V, single N-channel Trench MOSFET

16. Contents

General description	1
Features and benefits	1
Applications	1
Quick reference data	1
Pinning information	2
Ordering information	2
Marking	2
Limiting values	3
Thermal characteristics	5
Characteristics	7
Test information	11
Package outline	11
Soldering	12
Revision history	13
Legal information	14
Data sheet status	14
Definitions	14
Disclaimers	14
Trademarks	15
	General description Features and benefits Applications Quick reference data Pinning information Ordering information Marking Limiting values Thermal characteristics Characteristics Test information Package outline Soldering Revision history Legal information Data sheet status Definitions Disclaimers Trademarks

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